

Description

JMP N-channel Enhancement Mode Power MOSFET

Features

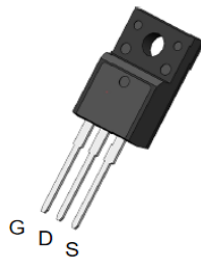
- 600V, 8A
 $R_{DS(ON)} < 0.74\Omega @ V_{GS} = 10V$
- Fast Switching
- Improved dv/dt Capability

Applications

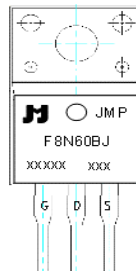
- Load Switch
- PWM Application
- Power Management



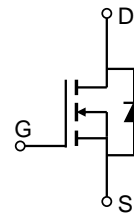
100% UIS TESTED!
100% ΔVds TESTED!



TO-220FP-3L Top View



Marking and Pin Assignment



Schematic Diagram

Package Marking and Ordering Information

Device Marking	Device	Outline	Package	TUBE (pcs)	Inner Box (pcs)	Per Carton (pcs)
JMPF8N60BJ	JMPF8N60BJ	TUBE	TO-220FP-3L	50	1000	5000

Absolute Maximum Ratings (@ $T_C = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Value	Units
V_{DS}	Drain-to-Source Voltage	600	V
V_{GS}	Gate-to-Source Voltage	± 30	V
I_D	Continuous Drain Current	$T_C = 25^\circ\text{C}$	8
		$T_C = 100^\circ\text{C}$	5
I_{DM}	Pulsed Drain Current ⁽¹⁾	32	A
E_{AS}	Single Pulsed Avalanche Energy ⁽²⁾	265	mJ
P_D	Power Dissipation	$T_C = 25^\circ\text{C}$	27
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient ⁽³⁾	55	$^\circ\text{C/W}$
$R_{\theta JC}$	Thermal Resistance, Junction to Case	4.7	
T_J, T_{STG}	Junction & Storage Temperature Range	-55 to 150	$^\circ\text{C}$



Electrical Characteristics (T_J = 25°C unless otherwise specified)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
Off Characteristics						
V _{(BR)DSS}	Drain-Source Breakdown Voltage	I _D = 250μA, V _{GS} = 0V	600	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 600V, V _{GS} = 0V	-	-	1.0	μA
I _{GSS}	Gate-Body Leakage Current	V _{DS} = 0V, V _{GS} = ±30V	-	-	±100	nA
On Characteristics						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 250μA	2	3	4	V
R _{DS(ON)}	Static Drain-Source ON-Resistance ⁽⁴⁾	V _{GS} = 10V, I _D = 4A	-	0.99	1.29	Ω
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{GS} = 0V, V _{DS} = 25V, f = 1MHz	-	1142	-	pF
C _{oss}	Output Capacitance		-	105	-	pF
C _{rss}	Reverse Transfer Capacitance		-	13	-	pF
Q _g	Total Gate Charge	V _{GS} = 0 to 10V V _{DS} = 300V, I _D = 4A	-	25	-	nC
Q _{gs}	Gate Source Charge		-	6	-	nC
Q _{gd}	Gate Drain ("Miller") Charge		-	8	-	nC
Switching Characteristics						
t _{d(on)}	Turn-On Delay Time	V _{GS} = 10V, V _{DD} = 300V I _D = 4A, R _{GEN} = 24Ω	-	20	-	ns
t _r	Turn-On Rise Time		-	23	-	ns
t _{d(off)}	Turn-Off Delay Time		-	80	-	ns
t _f	Turn-Off Fall Time		-	30	-	ns
Drain-Source Diode Characteristics and Max Ratings						
I _S	Maximum Continuous Drain to Source Diode Forward Current		-	-	8	A
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	32	A
V _{SD}	Drain to Source Diode Forward Voltage	V _{GS} = 0V, I _S = 8A	-	-	1.2	V
t _{rr}	Body Diode Reverse Recovery Time	I _F = 8A, di/dt = 100A/us	-	413.3	-	ns
Q _{rr}	Body Diode Reverse Recovery Charge		-	3.3	-	μC

- Notes:
1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature.
 2. E_{AS} condition: Starting T_J=25°C, V_{DD}=50V, V_G=10V, R_G=25ohm, L=10mH, I_{AS}=7.3A
 3. RθJA is measured with the device mounted on a minimum recommended pad of 2oz copper FR4 PCB
 4. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 0.5%.

Typical Performance Characteristics

Figure 1: Output Characteristics

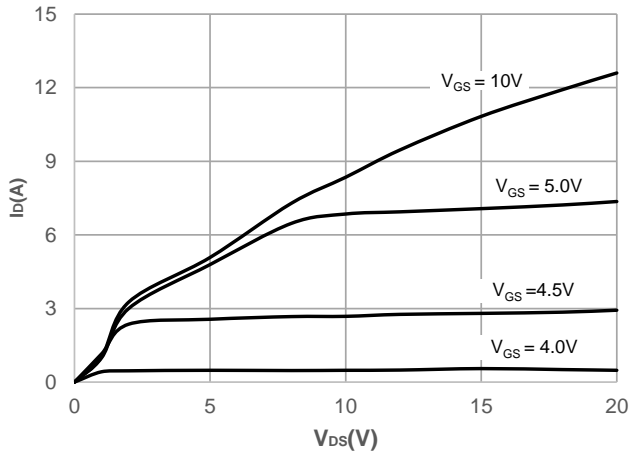


Figure 2: Typical Transfer Characteristics

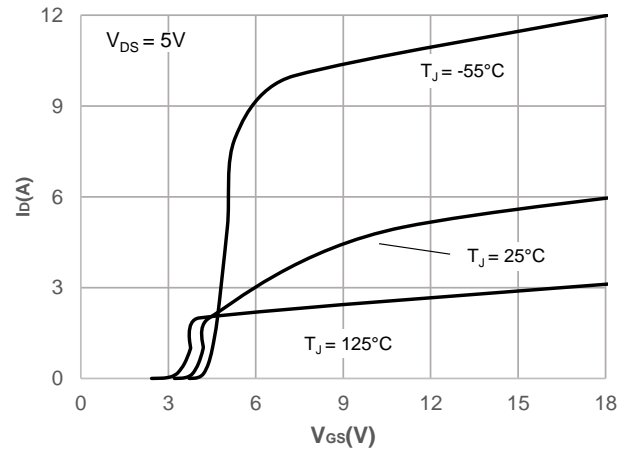


Figure 3: On-resistance vs. Drain Current

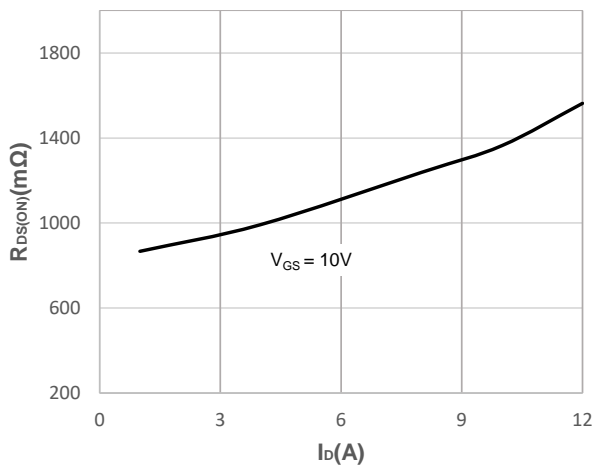


Figure 4: Body Diode Characteristics

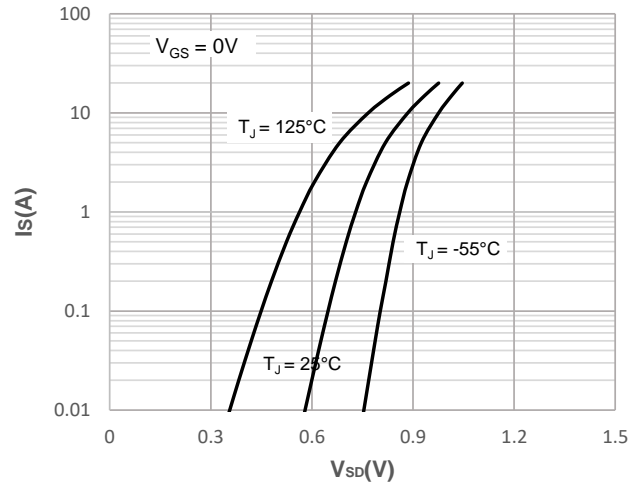


Figure 5: Gate Charge Characteristics

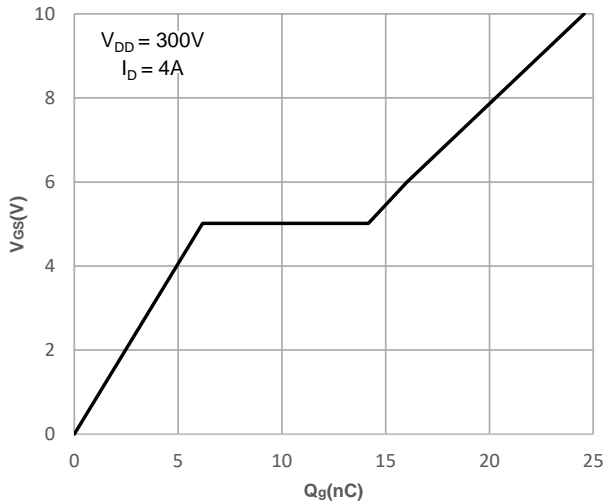
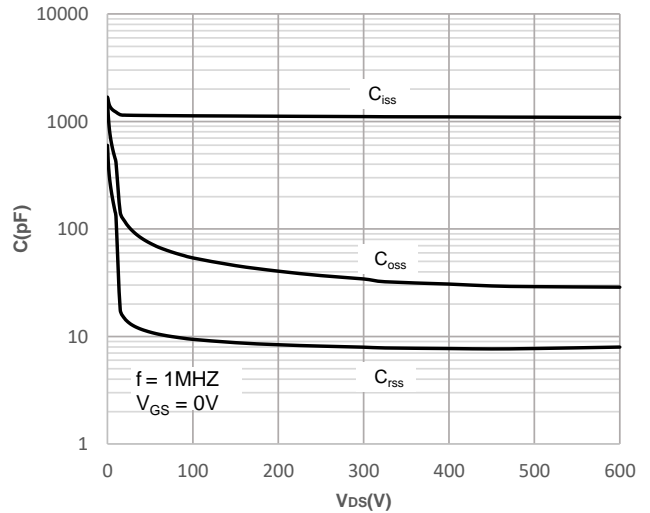


Figure 6: Capacitance Characteristics



Typical Performance Characteristics

Figure 7: Normalized Breakdown voltage vs. Junction Temperature

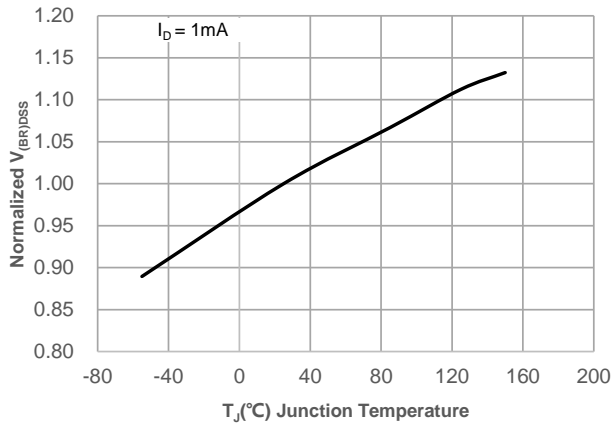


Figure 8: Normalized on Resistance vs. Junction Temperature

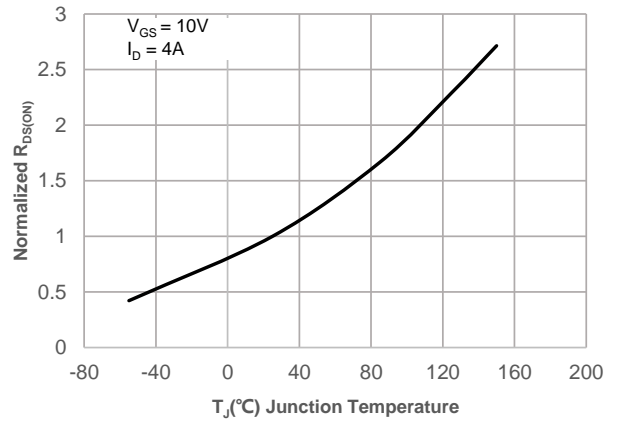


Figure 9: Maximum Safe Operating Area

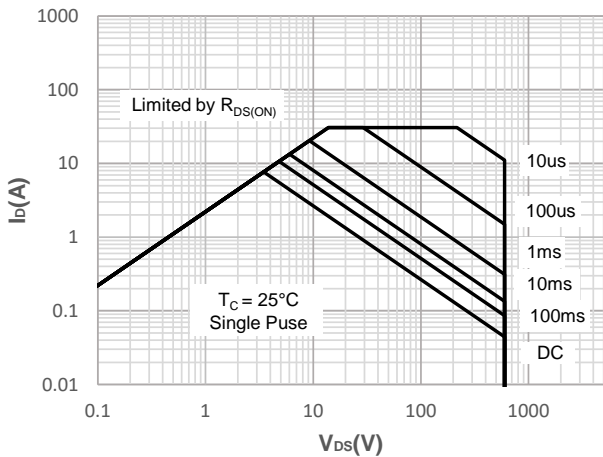


Figure 10: Maximum Continuous Driain Current vs. Case Temperature

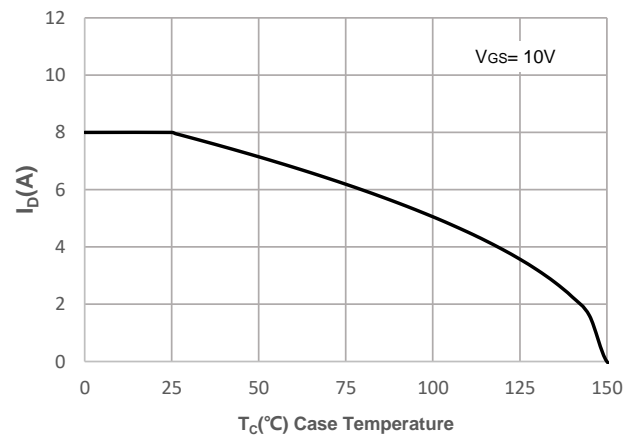


Figure 11: Normalized Maximum Transient Thermal Impedance

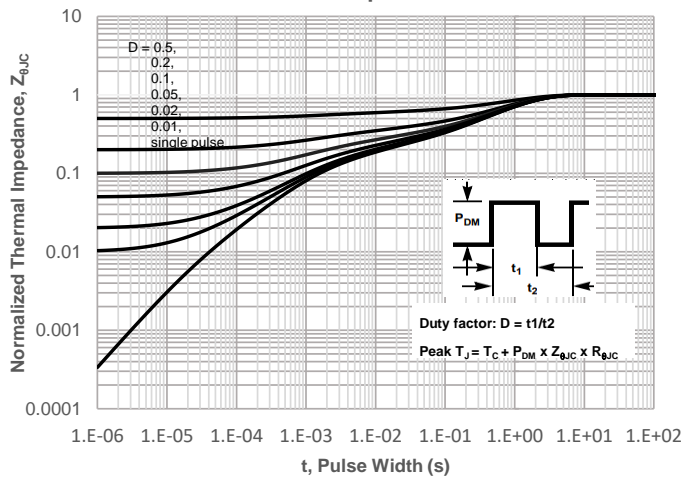
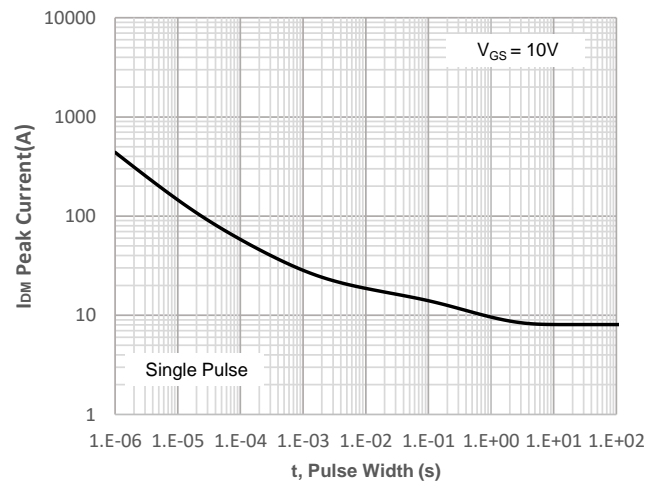


Figure 12: Peak Current Capacity



Test Circuit

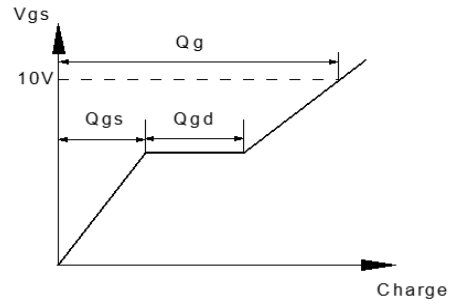
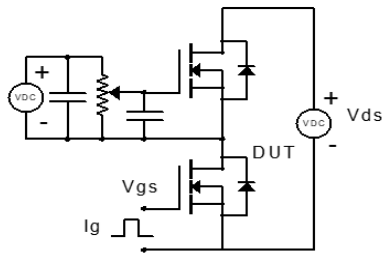


Figure 1: Gate Charge Test Circuit & Waveform

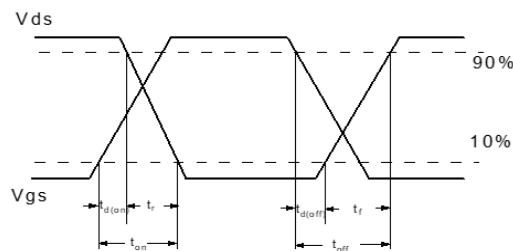
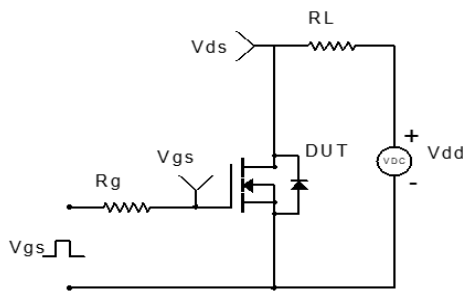


Figure 2: Resistive Switching Test Circuit & Waveform

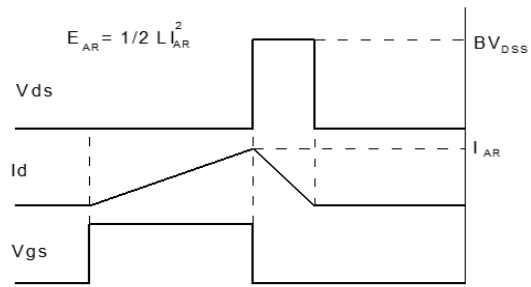
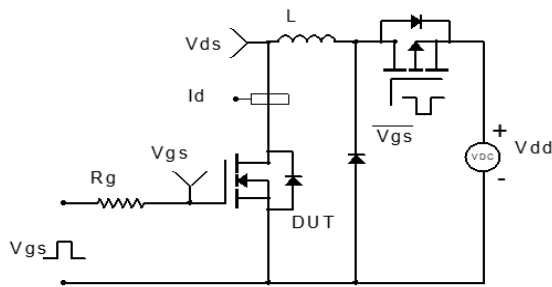


Figure 3: Unclamped Inductive Switching Test Circuit & Waveform

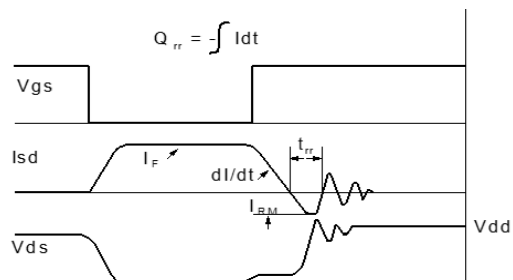
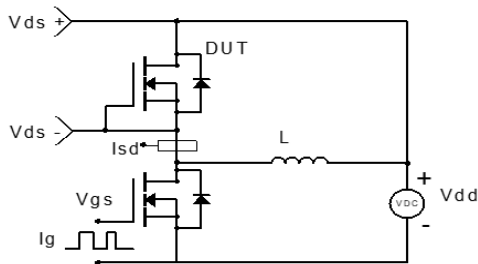
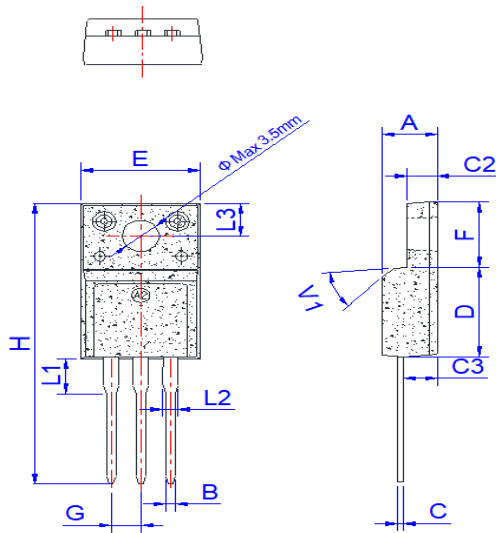



Figure 4: Diode Recovery Test Circuit & Waveform

Package Mechanical Data(TO-220FP-3L)



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.50		4.90	0.177		0.193
B	0.74	0.80	0.83	0.029	0.031	0.033
C	0.47		0.65	0.019		0.026
C2	2.45		2.75	0.096		0.108
C3	2.60		3.00	0.102		0.118
D	8.80		9.30	0.346		0.366
E	9.80		10.4	0.386		0.410
F	6.40		6.80	0.252		0.268
G		2.54			0.1	
H	28.0		29.8	1.102		1.173
L1		3.63			0.143	
L2	1.14		1.70	0.045		0.067
L3		3.30			0.130	
V1		45°			45°	

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